TOSHIBA Photocoupler GaAs IRed & Photo-Triac

TLP525G,TLP525G-2,TLP525G-4

Triac Drive
Programmable Controllers
AC-Output Module
Solid State Relay

The TOSHIBA TLP525G, -2 and -4 consist of a photo–triac optically coupled to a gallium arsenide infrared emitting diode.

The TLP525G-2 offers two isolated channels in an eight lead plastic DIP package, while the TLP525G-4 provides four isolated channels in a sixteen lead plastic DIP package.

• Peak off-stage voltage: 400V (min.)

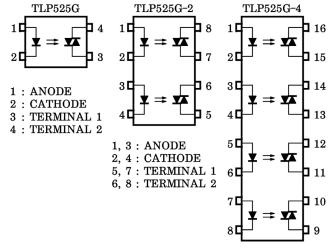
• Trigger LED current: 10mA (max.)

Peak on-stage current: 2Apk (max.)

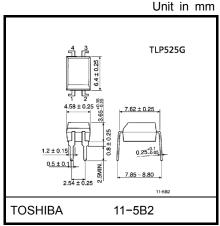
• Isolation voltage: 2500V_{rms} (min.)

• UL recognized: File no.E67349

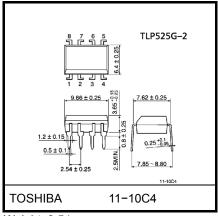
Pin Configurations (top view)



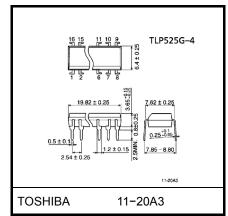
1, 3, 5, 7 : ANODE 2, 4, 6, 8 : CATHODE 9, 11, 13, 15 : TERMINAL 1 10, 12, 14, 16 : TERMINAL 2



Weight: 0.26g



Weight: 0.54g



Weight: 1.1g



Absolute Maximum Ratings (Ta = 25°C)

Characteristic				Ra		
			Symbol	TLP525G	TLP525G–2 TLP525G–4	Unit
ΓED	Forward current		lF	50	50	mA
	Forward current derating		I _F / °C	–0.7 (Ta ≥ 53°C)	–0.5 (Ta ≥ 25°C)	mA / °C
	Pulse forward current		I _{FP}	1 (100µs pulse, 100pps)		Α
	Reverse voltage		V _R	5		V
	Junction temperature		Tj	125		°C
	Off-state output terminal voltage		V_{DRM}	400		V
	On-state RMS current	Ta = 25°C	l=	100	80	- mA
		Ta = 70°C	I _{T (RMS)}	50	40	IIIA
Detector	On–state current derating (Ta≥25°C)		I _T / °C	-1.1 -0.9		mA / °C
	Peak on state current		I _{TP}	2 (100µs pulse, 120pps)		Α
	Peak nonrepetitive surge current (P _W = 10ms, DC = 10%)		I _{TSM}	1.2		А
	Junction temperature		Tj	115		°C
Storage temperature range			T _{stg}	−55~125		°C
Operating temperature range			T _{opr}	-40~100		°C
Lead soldering temperature			T _{sol}	260 (10s)		°C
Isolation voltage (Note)		BVS	2500 (AC, 1min., R.H. ≤ 60%)		V _{rms}	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	120	Vac
Forward current	l _F	15	20	25	mA
Peak on-state current	I _{TP}	_	_	1	Α
Operating temperature	T _{opr}	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.



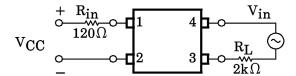
Individual Electrical Characteristics (Ta = 25°C)

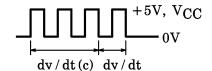
Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
CED	Forward voltage	V _F	I _F = 10mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1MHz	_	30	_	pF
	Peak off-state current	I _{DRM}	V _{DRM} = 400V	_	10	100	nA
	Peak on-state voltage	V_{TM}	I _{TM} = 100mA	_	1.7	3.0	V
Detector	Holding current	lΗ	_	_	0.2		mA
	Critical rate of rise of off–state voltage	dv / dt	$V_{in} = 120V_{rms}$, Ta = 85°C (Figure 1)	200	500	ı	V / μs
	Critical rate of rise of commutating voltage	dv / dt (c)	$V_{in} = 30V_{rms}$, $I_T = 15mA$ (Figure 1)	_	0.2		V / µs

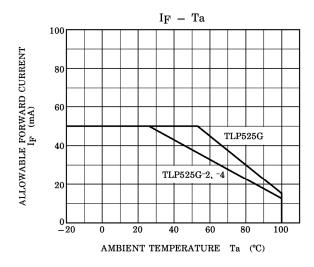
Coupled Electrical Characteristics (Ta = 25°C)

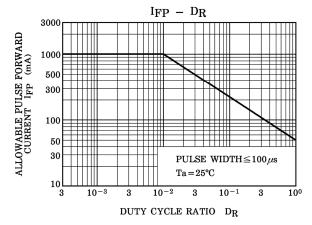
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	V _T = 3V	_	5	10	mA
Capacitance input to output	CS	V _S = 0, f = 1MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω
	BVS	AC, 1 minute	2500	_	_	- Vrms
Isolation voltage		AC, 1 second, in oil	_	5000	_	
		DC, 1 minute, in oil	_	5000	_	Vdc

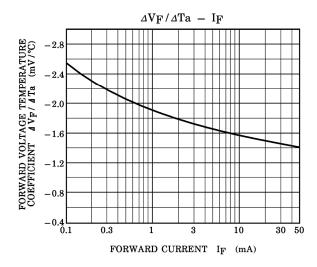
Fig.1 dv / dt Test Circuit

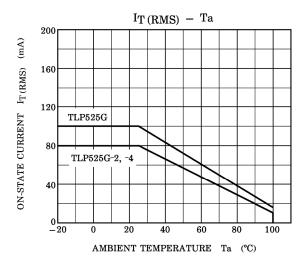


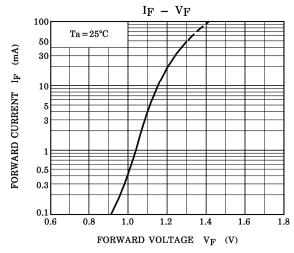


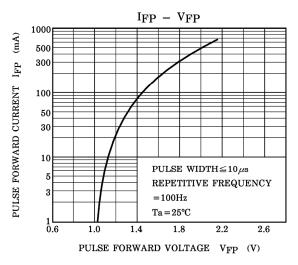


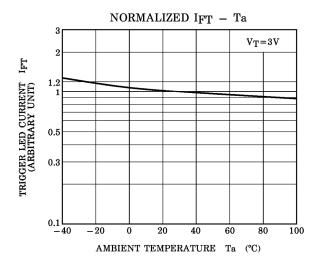


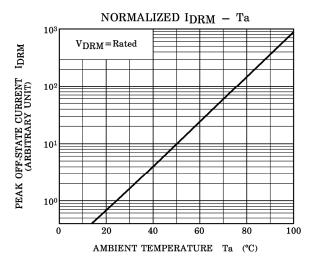


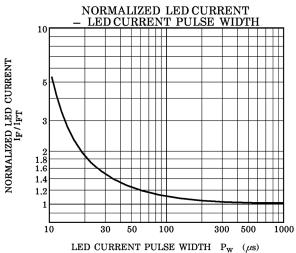


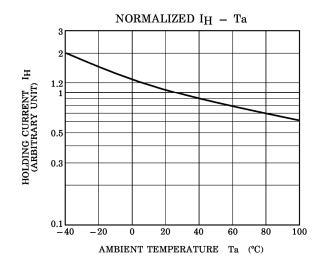


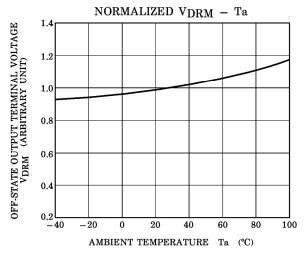












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